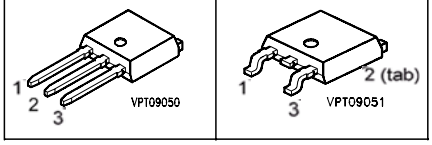
Cool MOS™ Power Transistor

V_{DS} @ T_{jmax}	650	V
$R_{DS(on)}$	0.95	Ω
I_D	4.5	A

Feature

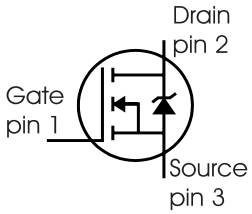
- New revolutionary high voltage technology
- Ultra low gate charge
- Periodic avalanche rated
- Extreme d*v*/d*t* rated
- High peak current capability
- Improved transconductance

PG-TO251 PG-TO252



- Pb-free lead plating; RoHS compliant, available in Halogen free mold compound[a)]
- Fully qualified according to JEDEC for Industrial Applications

Type	Package	Marking
SPD04N60C3	PG-TO252	04N60C3
SPU04N60C3	PG-TO251	04N60C3



Maximum Ratings

Parameter	Symbol	Value	Unit
Continuous drain current T_C = 25 °C T_C = 100 °C	I_D	 4.5 2.8	A
Pulsed drain current, t_p limited by T_{jmax}	$I_{D\ puls}$	13.5	
Avalanche energy, single pulse I_D = 3.4 A, V_{DD} = 50 V	E_{AS}	130	mJ
Avalanche energy, repetitive t_{AR} limited by T_{jmax}[1] I_D = 4.5 A, V_{DD} = 50 V	E_{AR}	0.4	
Avalanche current, repetitive t_{AR} limited by T_{jmax}	I_{AR}	4.5	A
Gate source voltage static	V_{GS}	±20	V
Gate source voltage AC (f >1Hz)	V_{GS}	±30	
Power dissipation, T_C = 25°C	P_{tot}	50	W
Operating and storage temperature	T_j, T_{stg}	-55... +150	°C
Reverse diode dv/dt [5)]	dv/dt	15	V/ns

[a)] non-Halogen free (OPN: SPD04N60C3BT), Halogen free (OPN: SPD04N60C3AT)

Maximum Ratings

Parameter	Symbol	Value	Unit
Drain Source voltage slope V_{DS} = 480 V, I_D = 4.5 A, T_j = 125 °C	dv/dt	50	V/ns

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Thermal resistance, junction - case	R_{thJC}	-	-	2.5	K/W
Thermal resistance, junction - ambient, leaded	R_{thJA}	-	-	75	
SMD version, device on PCB: @ min. footprint @ 6 cm^2 cooling area [2)]	R_{thJA}	 - -	 - -	 75 50	
Soldering temperature, *) 1.6 mm (0.063 in.) from case for 10s	T_{sold}	-	-	260	°C

Electrical Characteristics, at T_j=25°C unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=0.25mA	600	-	-	V
Drain-Source avalanche breakdown voltage	$V_{(BR)DS}$	V_{GS}=0V, I_D=4.5A	-	700	-	
Gate threshold voltage	$V_{GS(th)}$	I_D=200µA, V_{GS}=V_{DS}	2.1	3	3.9	
Zero gate voltage drain current	I_{DSS}	V_{DS}=600V, V_{GS}=0V, T_j=25°C, T_j=150°C	 - -	 0.5 -	 1 50	µA
Gate-source leakage current	I_{GSS}	V_{GS}=30V, V_{DS}=0V	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=2.8A, T_j=25°C T_j=150°C	 - -	 0.85 2.3	 0.95 -	Ω
Gate input resistance	R_G	f=1MHz, open Drain	-	0.95	-	

*) TO252: reflow soldering, MSL1; TO251: wavesoldering

Electrical Characteristics , at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Transconductance	g_{fs}	V_{DS}≥2*I_D*$R_{DS(on)max}$, I_D=2.8A	-	4.4	-	S
Input capacitance	C_{iss}	V_{GS}=0V, V_{DS}=25V, f=1MHz	-	490	-	pF
Output capacitance	C_{oss}		-	160	-	
Reverse transfer capacitance	C_{rss}		-	15	-	
Effective output capacitance,[3] energy related	$C_{o(er)}$	V_{GS}=0V, V_{DS}=0V to 480V	-	20	-	pF
Effective output capacitance,[4] time related	$C_{o(tr)}$		-	35	-	
Turn-on delay time	$t_{d(on)}$	V_{DD}=380V, V_{GS}=0/10V, I_D=4.5A, R_G=18Ω	-	6	-	ns
Rise time	t_r		-	2.5	-	
Turn-off delay time	$t_{d(off)}$		-	58.5	80	
Fall time	t_f		-	9.5	14	

Gate Charge Characteristics

Gate to source charge	Q_{gs}	V_{DD}=480V, I_D=4.5A	-	2.2	-	nC
Gate to drain charge	Q_{gd}		-	8.8	-	
Gate charge total	Q_g	V_{DD}=480V, I_D=4.5A, V_{GS}=0 to 10V	-	19	25	
Gate plateau voltage	$V_{(plateau)}$	V_{DD}=480V, I_D=4.5A	-	5	-	V

[1] Repetitve avalanche causes additional power losses that can be calculated as P_{AV}=E_{AR}*f.

[2] Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical without blown air.

[3] $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.

[4] $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.

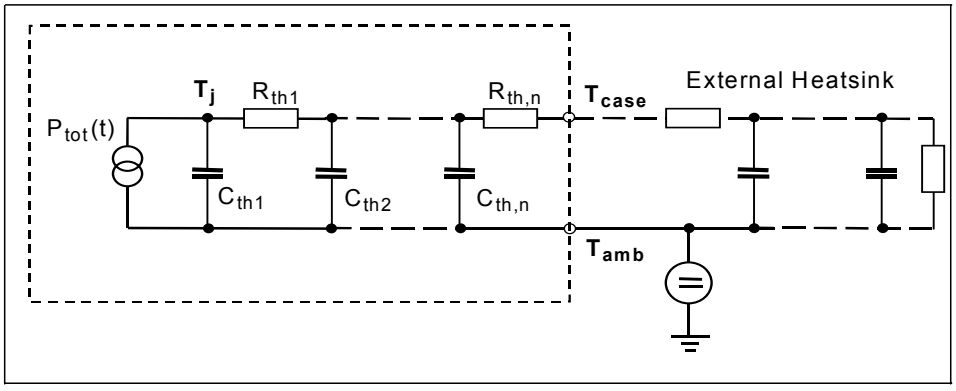
[5] I_{SD}<=I_D, di/dt<=400A/us, V_{DClink}=400V, V_{peak}<$V_{BR, DSS}$, T_j<$T_{j,max}$.
Identical low-side and high-side switch.

Electrical Characteristics, at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Inverse diode continuous forward current	I_S	T_C=25°C	-	-	4.5	A
Inverse diode direct current, pulsed	I_{SM}		-	-	13.5	
Inverse diode forward voltage	V_{SD}	V_{GS}=0V, I_F=I_S	-	1	1.2	V
Reverse recovery time	t_{rr}	V_R=480V, I_F=I_S ,	-	300	500	ns
Reverse recovery charge	Q_{rr}	di_F/dt=100A/µs	-	2.6	-	µC
Peak reverse recovery current	I_{rrm}		-	18	-	A
Peak rate of fall of reverse recovery current	di_{rr}/dt		-	-	900	A/µs

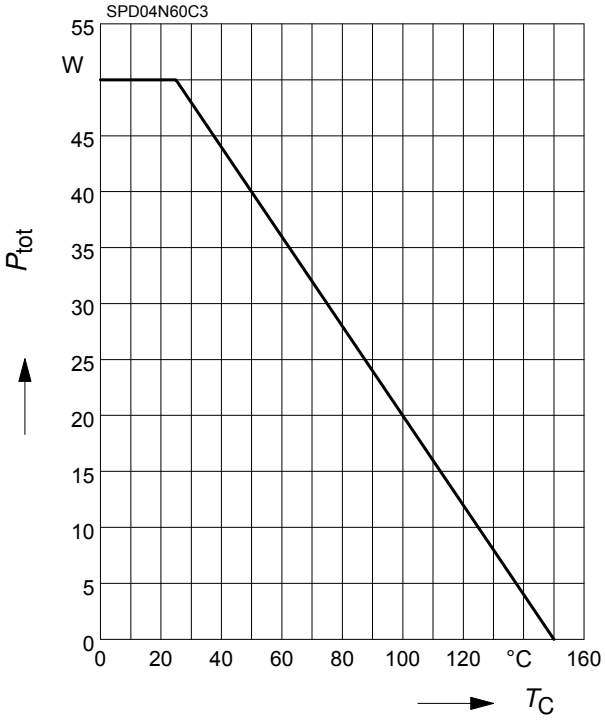
Typical Transient Thermal Characteristics

Symbol	Value	Unit	Symbol	Value	Unit
	typ.			typ.	
Thermal resistance			Thermal capacitance		
R_{th1}	0.039	K/W	C_{th1}	0.00007347	Ws/K
R_{th2}	0.074		C_{th2}	0.0002831	
R_{th3}	0.132		C_{th3}	0.0004062	
R_{th4}	0.555		C_{th4}	0.001215	
R_{th5}	0.529		C_{th5}	0.00276	
R_{th6}	0.169		C_{th6}	0.029	



1 Power dissipation

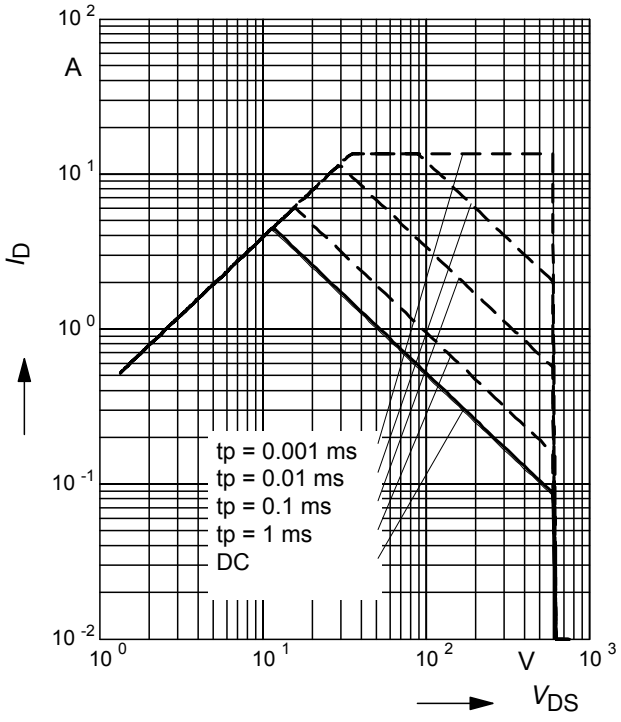
$P_{tot} = f(T_C)$



2 Safe operating area

$I_D = f(V_{DS})$

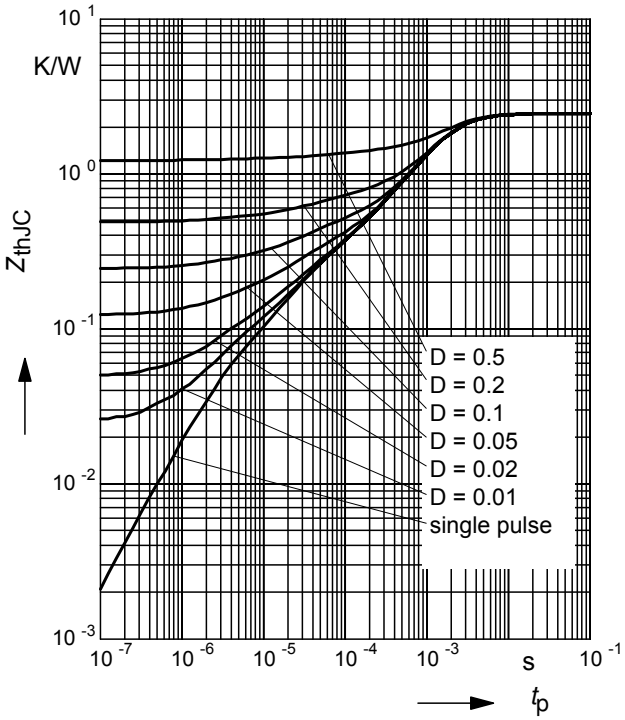
parameter : $D = 0$, T_C=25°C



3 Transient thermal impedance

$Z_{thJC} = f(t_p)$

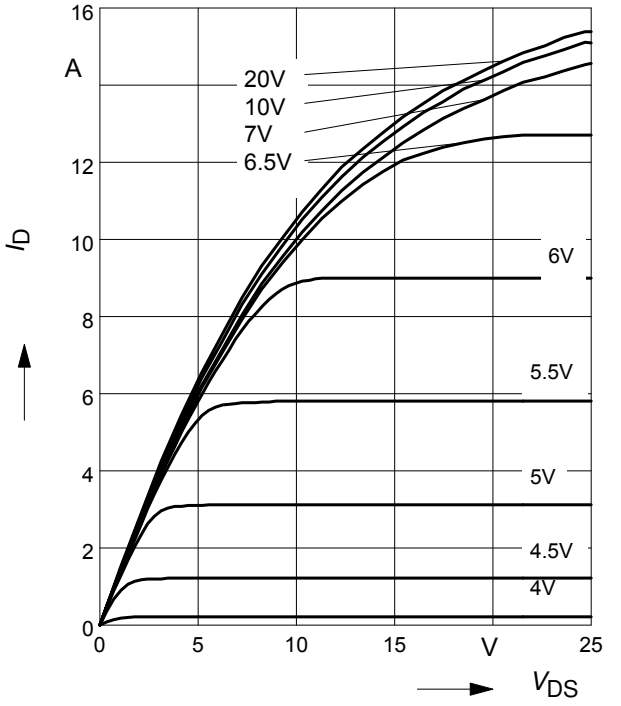
parameter: $D = t_p/T$



4 Typ. output characteristic

$I_D = f(V_{DS})$; T_j=25°C

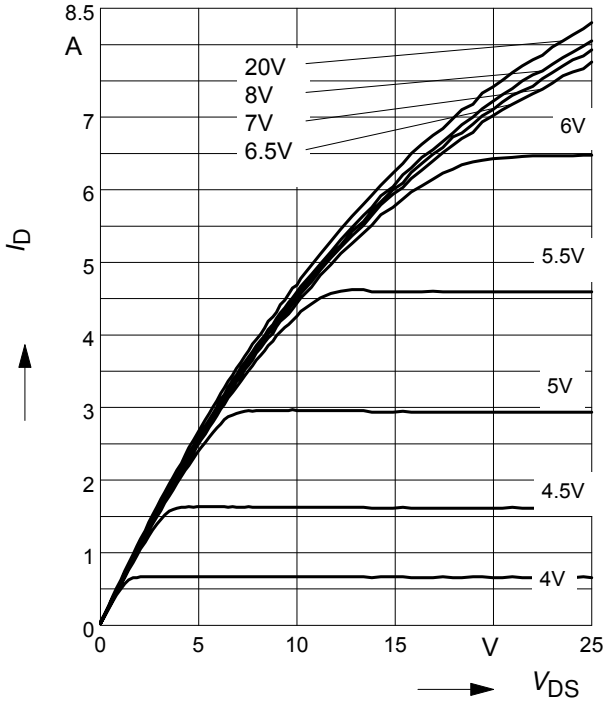
parameter: t_p = 10 µs, V_{GS}



5 Typ. output characteristic

$I_D = f(V_{DS})$; T_j=150°C

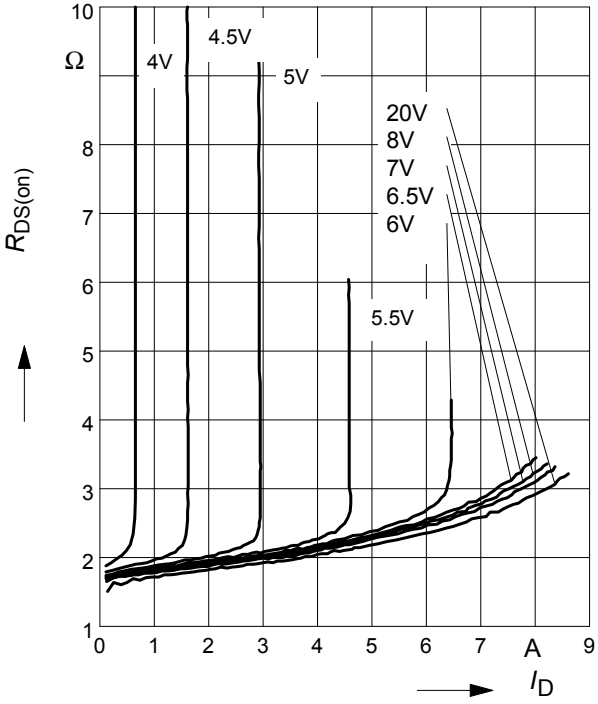
parameter: t_p = 10 µs, V_{GS}



6 Typ. drain-source on resistance

$R_{DS(on)}=f(I_D)$

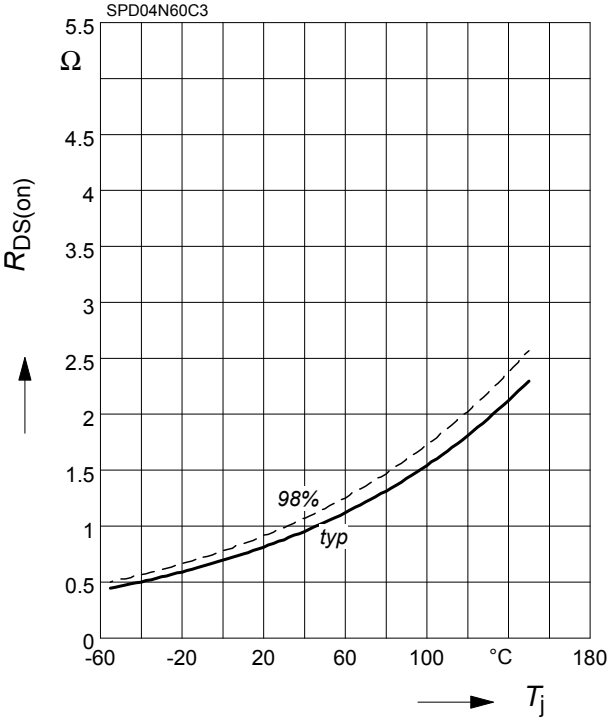
parameter: T_j=150°C, V_{GS}



7 Drain-source on-state resistance

$R_{DS(on)} = f(T_j)$

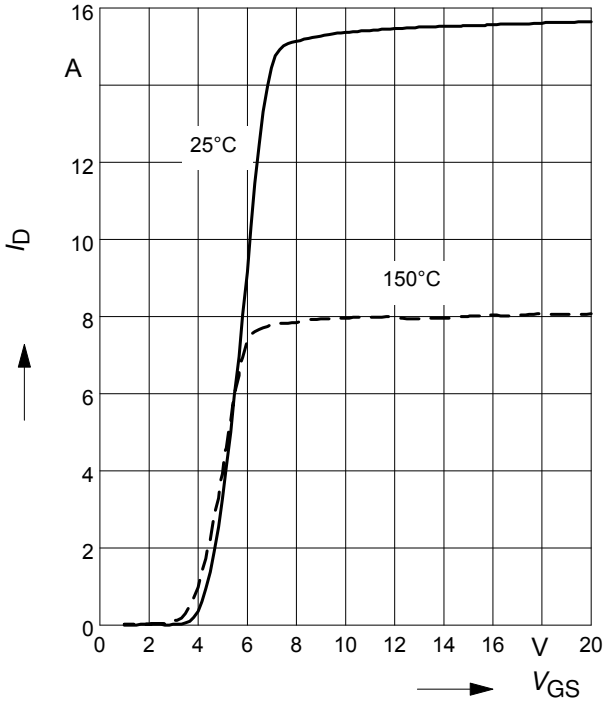
parameter : I_D = 2.8 A, V_{GS} = 10 V



8 Typ. transfer characteristics

$I_D = f(V_{GS})$; $V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$

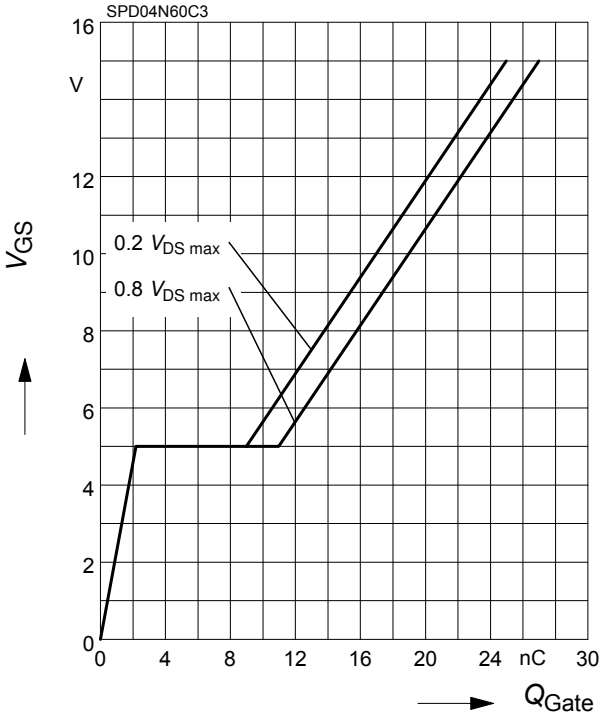
parameter: t_p = 10 µs



9 Typ. gate charge

$V_{GS} = f\ (Q_{Gate})$

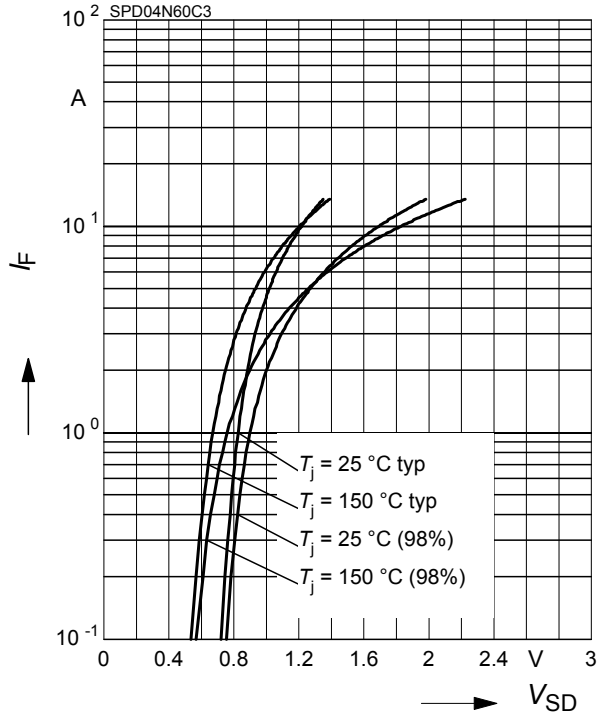
parameter: I_D = 4.5 A pulsed



10 Forward characteristics of body diode

$I_F = f\ (V_{SD})$

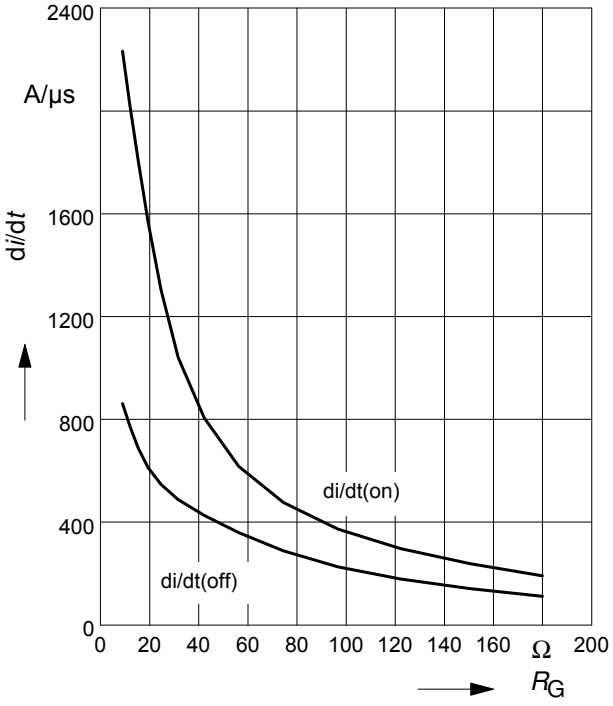
parameter: T_j , tp = 10 µs



11 Typ. drain current slope

d*i*/d*t* = f(R_G), inductive load, T_j = 125°C

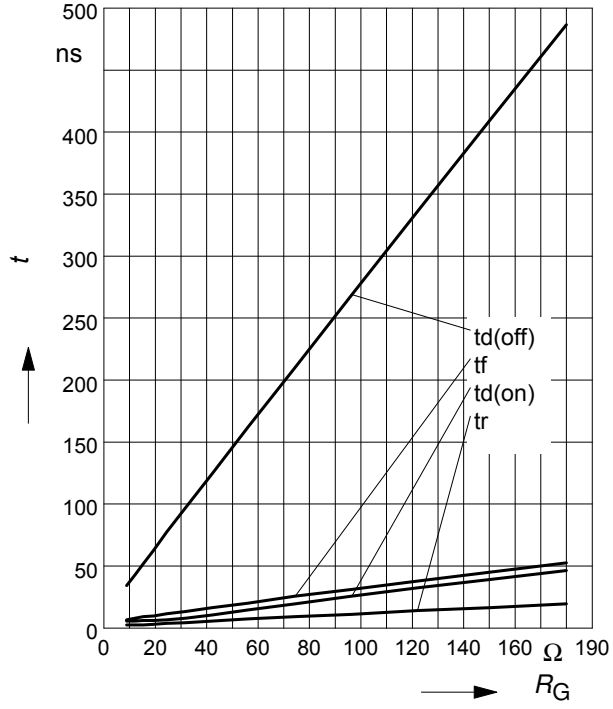
par.: V_{DS}=380V, V_{GS}=0/+13V, I_D=4.5A



12 Typ. switching time

$t = f\ (R_G)$, inductive load, T_j=125°C

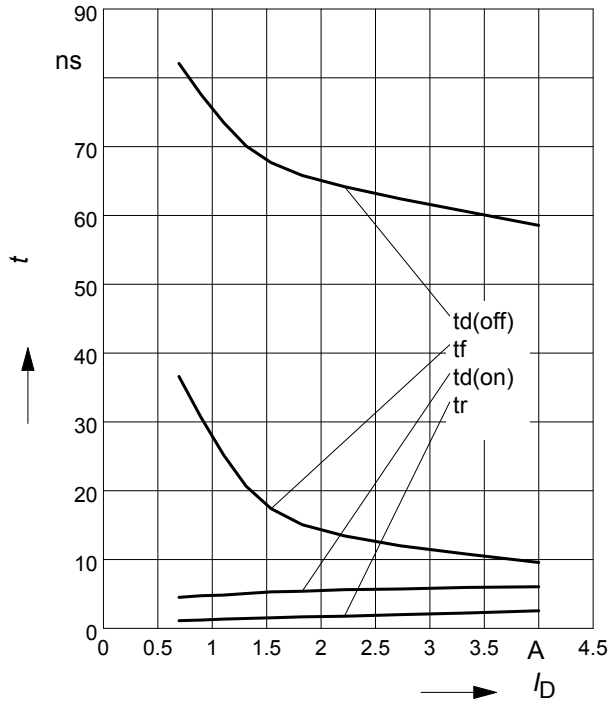
par.: V_{DS}=380V, V_{GS}=0/+13V, I_D=4.5 A



13 Typ. switching time

$t = f(I_D)$, inductive load, T_j=125°C

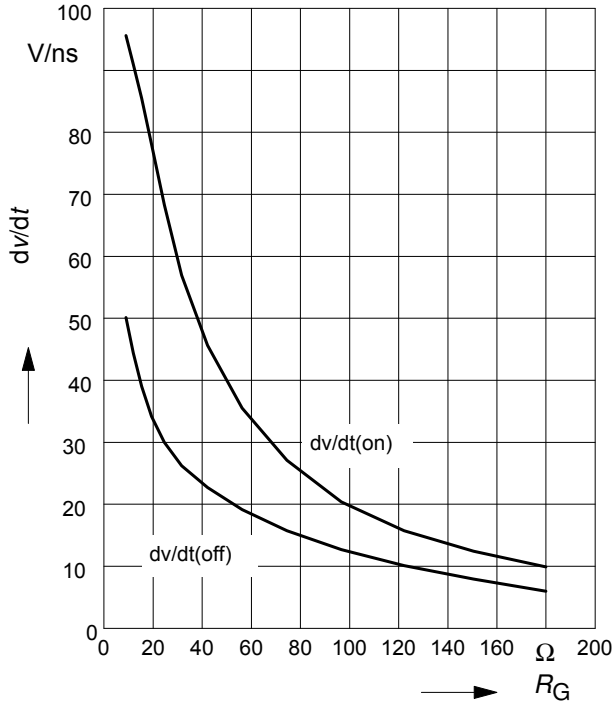
par.: V_{DS}=380V, V_{GS}=0/+13V, R_G=18Ω



14 Typ. drain source voltage slope

dv/dt = f(R_G), inductive load, T_j = 125°C

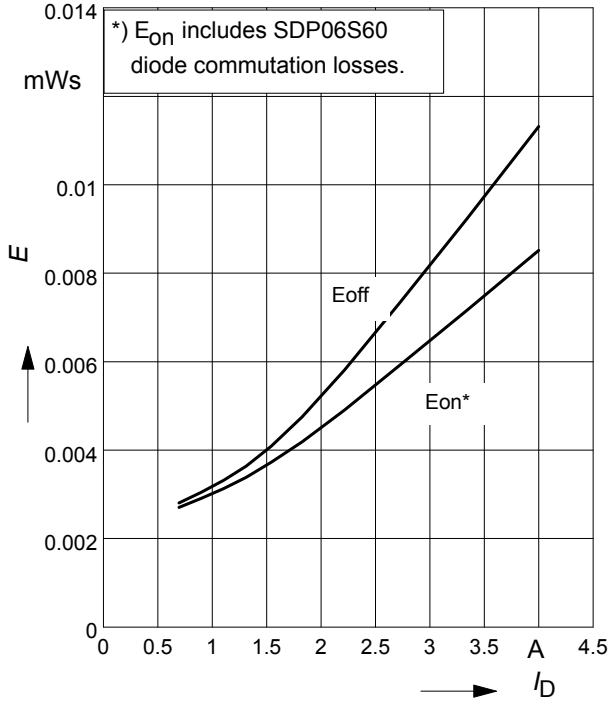
par.: V_{DS}=380V, V_{GS}=0/+13V, I_D=4.5A



15 Typ. switching losses

$E = f(I_D)$, inductive load, T_j=125°C

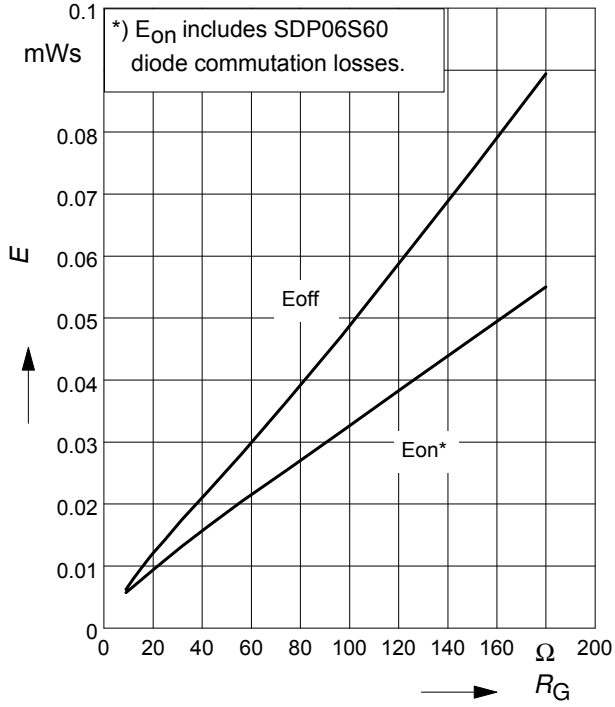
par.: V_{DS}=380V, V_{GS}=0/+13V, R_G=18Ω



16 Typ. switching losses

$E = f(R_G)$, inductive load, T_j=125°C

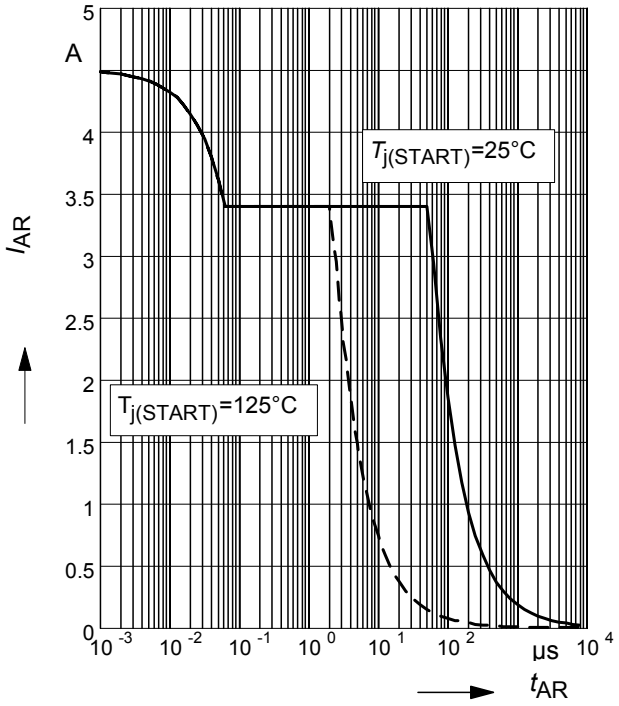
par.: V_{DS}=380V, V_{GS}=0/+13V, I_D=4.5A



17 Avalanche SOA

$I_{AR} = f(t_{AR})$

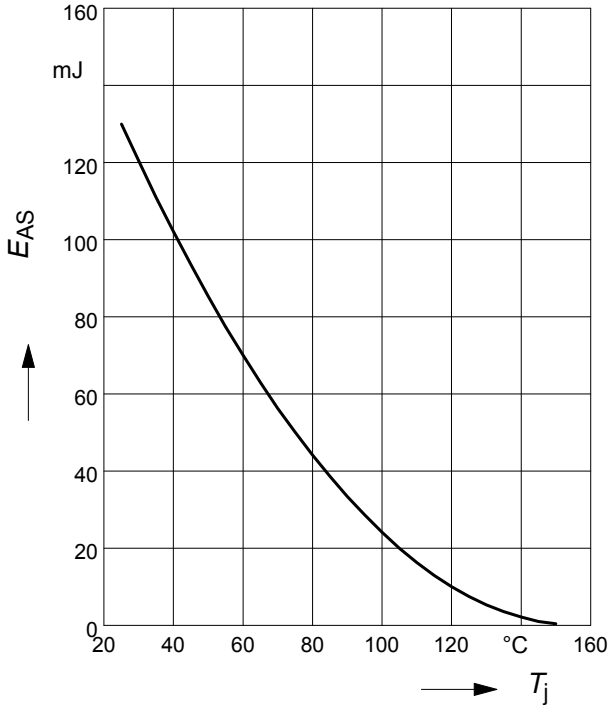
par.: $T_j \leq 150$ °C



18 Avalanche energy

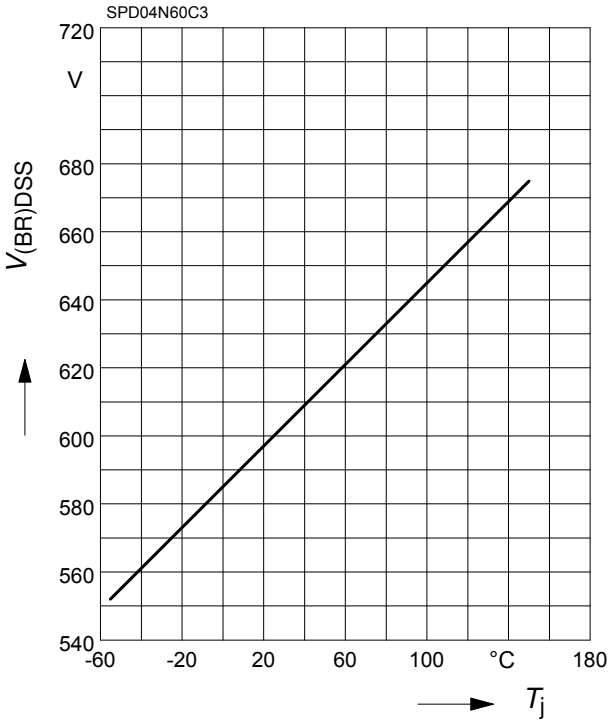
$E_{AS} = f(T_j)$

par.: I_D = 3.4 A, V_{DD} = 50 V



19 Drain-source breakdown voltage

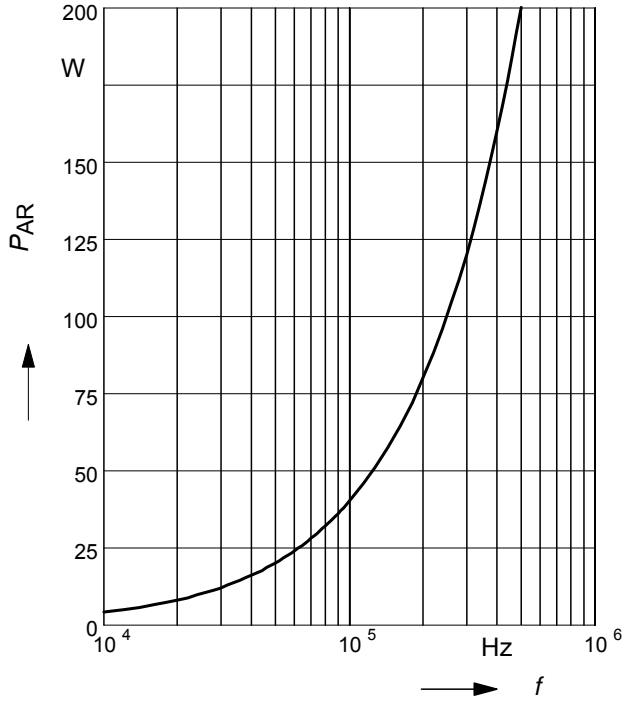
$V_{(BR)DSS} = f(T_j)$



20 Avalanche power losses

$P_{AR} = f(f)$

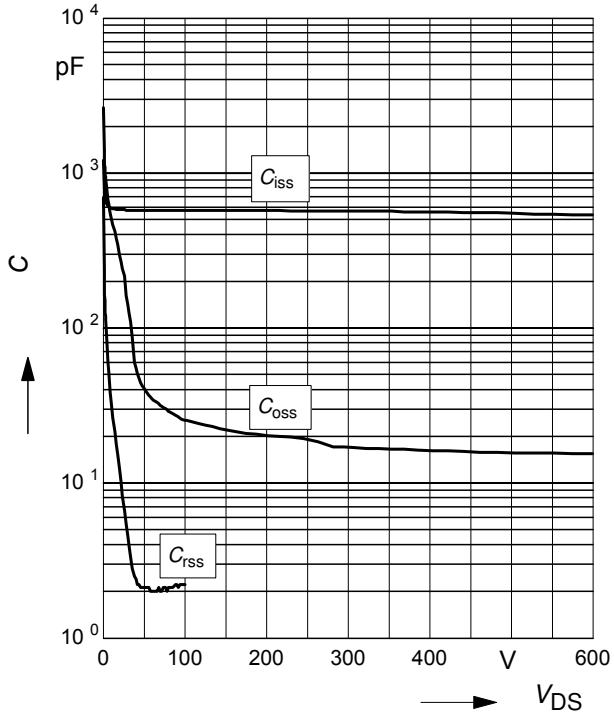
parameter: E_{AR}=0.4mJ



21 Typ. capacitances

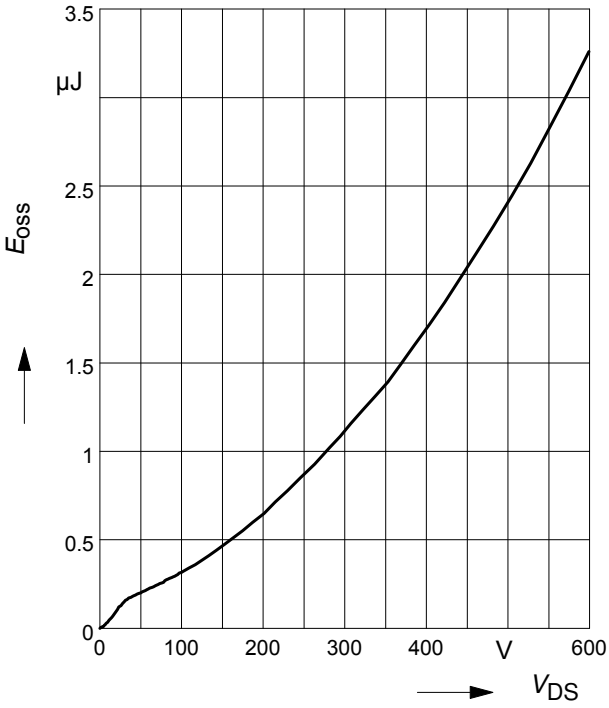
$C = f(V_{DS})$

parameter: V_{GS}=0V, f=1 MHz

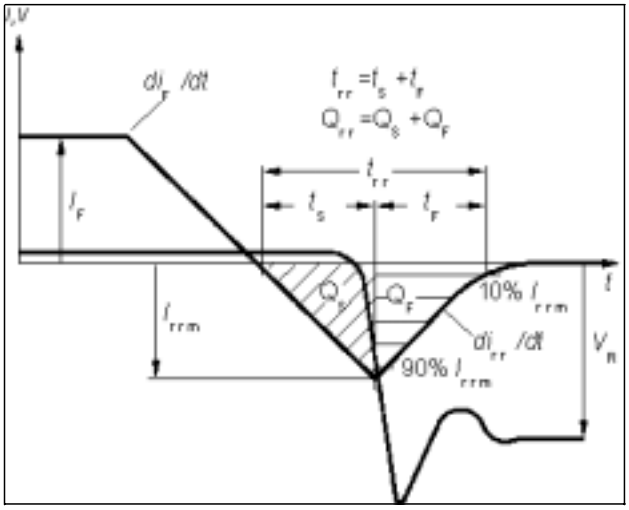


22 Typ. C_{oss} stored energy

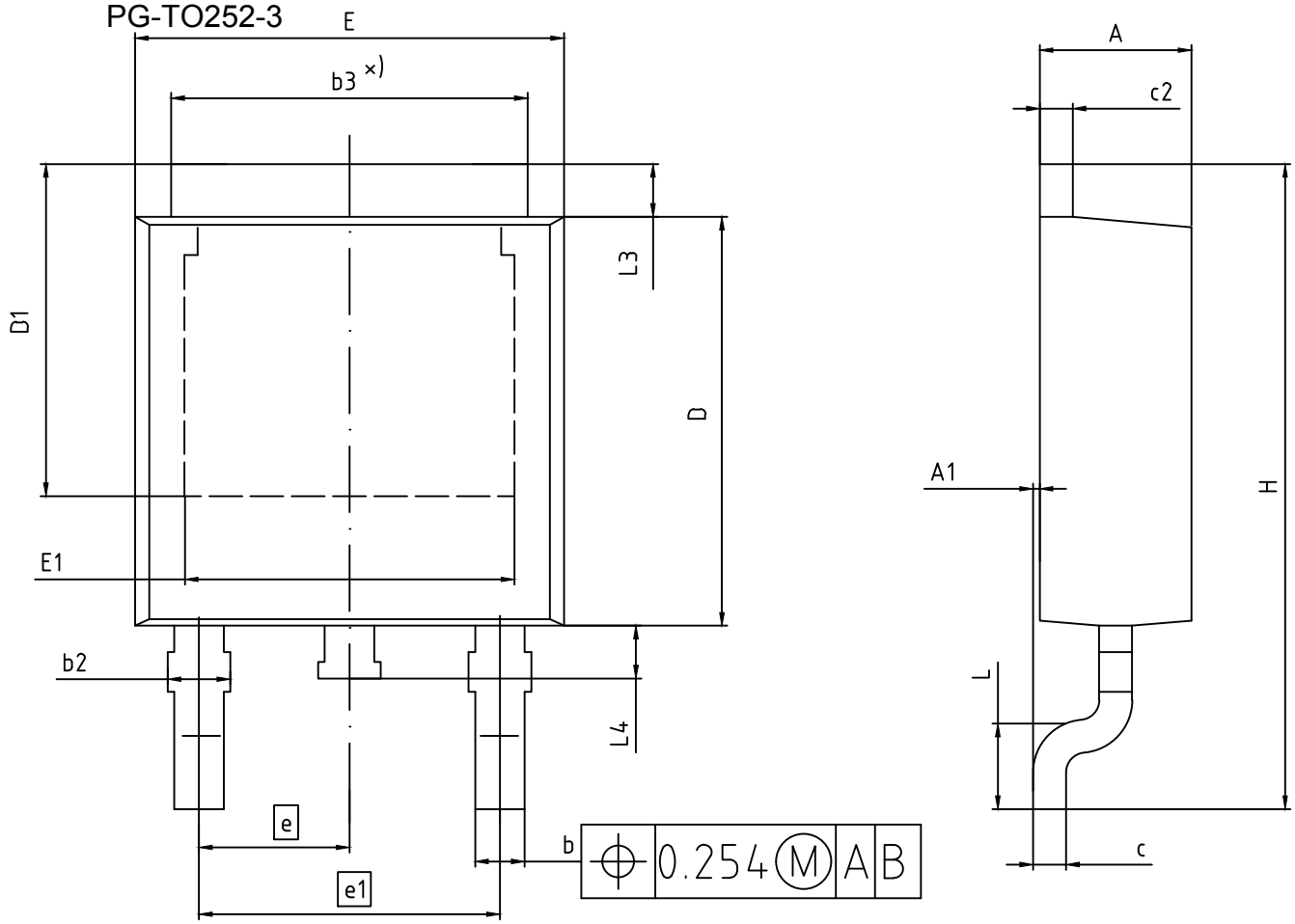
$E_{oss}=f(V_{DS})$

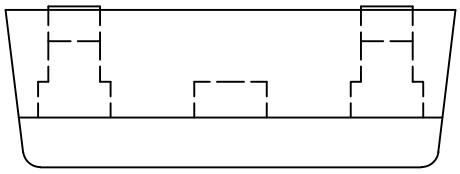


Definition of diodes switching characteristics



PG-TO252-3



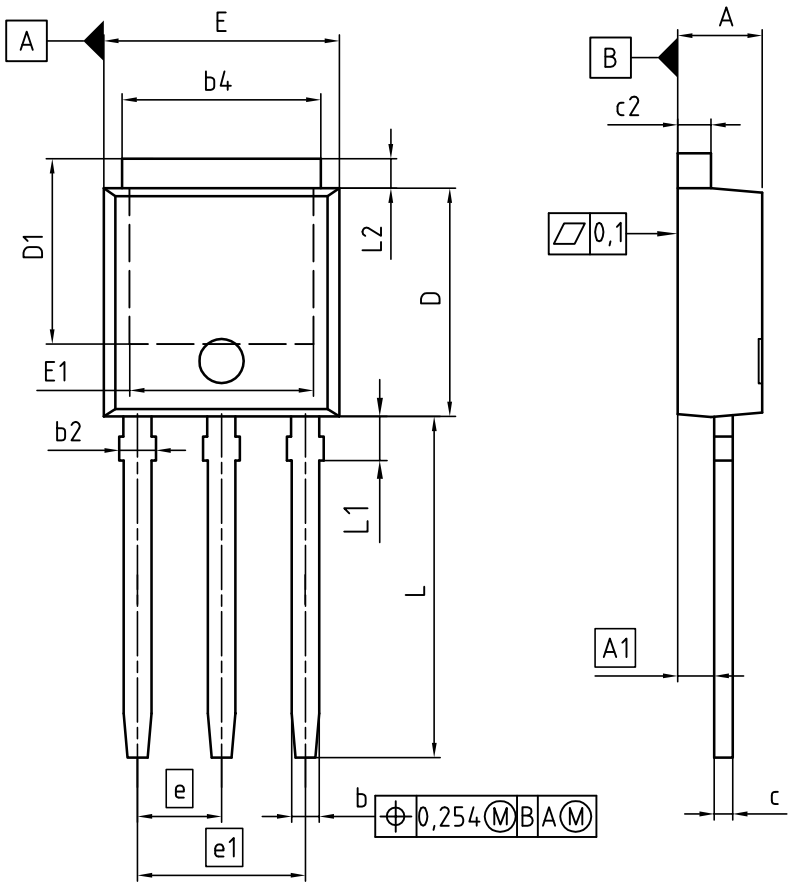


ALL DIMENSIONS REFER TO JEDEC STANDARD TO-252 AND DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS.

DIMENSION	MILLIMETERS	
	MIN.	MAX.
A	2.16	2.41
A1	0.00	0.15
b	0.64	0.89
b2	0.65	1.15
b3	4,95	5.50
c	0.46	0.61
c2	0.40	0.98
D	5.97	6.22
D1	5.02	5.84
E	6.35	6.73
E1	4.32	5.50
e	2.29	
e1	4.57	
N	3	
H	9.40	10.48
L	1.18	1.78
L3	0.89	1.27
L4	0.51	1.02

DOCUMENT NO.	Z8B00003328
REVISION	07
SCALE:	10:1
	0 1 2mm
EUROPEAN PROJECTION	
ISSUE DATE	01.04.2020

PG-TO251-3



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.16	2.41	0.085	0.095
A1	0.90	1.14	0.035	0.045
b	0.64	0.89	0.025	0.035
b2	0.65	1.15	0.026	0.045
b4	4.95	5.50	0.195	0.217
c	0.46	0.60	0.018	0.024
c2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	5.04	5.77	0.198	0.227
E	6.35	6.73	0.250	0.265
E1	4.70	5.21	0.185	0.205
e	2.29		0.090	
e1	4.57		0.180	
N	3		3	
L	8.89	9.65	0.350	0.380
L1	1.90	2.29	0.075	0.090
L2	0.89	1.37	0.035	0.054

DOCUMENT NO.	Z8B00003830
SCALE	0 2.0 0 2.0 4mm
EUROPEAN PROJECTION	
ISSUE DATE	19-03-2008
REVISION	03

Revision History

SPD04N60C3

Revision: 2020-05-26, Rev. 2.6

Previous Revision		
Revision	Date	Subjects (major changes since last revision)
2.6	2020-05-26	Update package outline

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Warnings
Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office.
The Infineon Technologies component described in this Data Sheet may be used in life-support devices or systems and/or automotive, aviation and aerospace applications or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support, automotive, aviation and aerospace device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

ENTEGRECİ

Bu belge www.entegreci.com üzerinden sunulmaktadır.

Elektronik komponent tedarikinde Entegreci

Entegreci, Eskişehir merkezli, Türkiye geneline satış yapan bir elektronik komponent mağazasıdır. Entegreler (IC), mikrodenetleyiciler, transistörler, diyotlar, pasif elemanlar, konnektörler, modüller ve geliştirme kartları tek adetten seri üretim adetlerine kadar satılır. Ürün sayfalarında güncel stok durumunu, fiyatı ve datasheet bağlantısını bulabilirsiniz.

Parça koduyla arama

Üretici parça numarasını yazın; stok ve fiyatı hemen görün.

www.entegreci.com

Ürün kategorileri

Entegreden kapasitöre tüm elektronik komponent kategorileri.

Kategorilere göz atın

Üreticiler

Aradığınız üreticinin ürünlerini tek sayfada inceleyin.

Üreticileri görün

Toplu alım ve teklif

Listede olmayan ya da yüksek adetli parçalar için teklif isteyin.

Teklif isteyin

www.entegreci.com | **destek@entegreci.com** | **0850 305 90 34**

Entegreci is an online electronic components store based in Türkiye. Search by manufacturer part number to see stock, prices and datasheets for integrated circuits, microcontrollers, transistors, passive components and connectors, or request a quote for parts that are not listed.

Bu sayfa Entegreci tarafından eklenmiştir. Belgenin önceki sayfaları asıl yayıncısına aittir ve içeriği değiştirilmemiştir; en güncel sürüm için belgenin yayıncısına başvurun.